

FX6ASJ-03

High-Speed Switching Use Pch Power MOS FET

REJ03G0247-0200 Rev.2.00 Nov 21, 2006

Features

• Drive voltage: 4 V

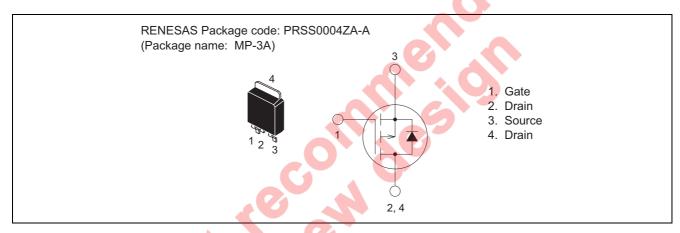
• V_{DSS} : -30 V

• $r_{DS(ON) (max)}$: 0.29 Ω

• $I_D: -6 A$

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 40 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

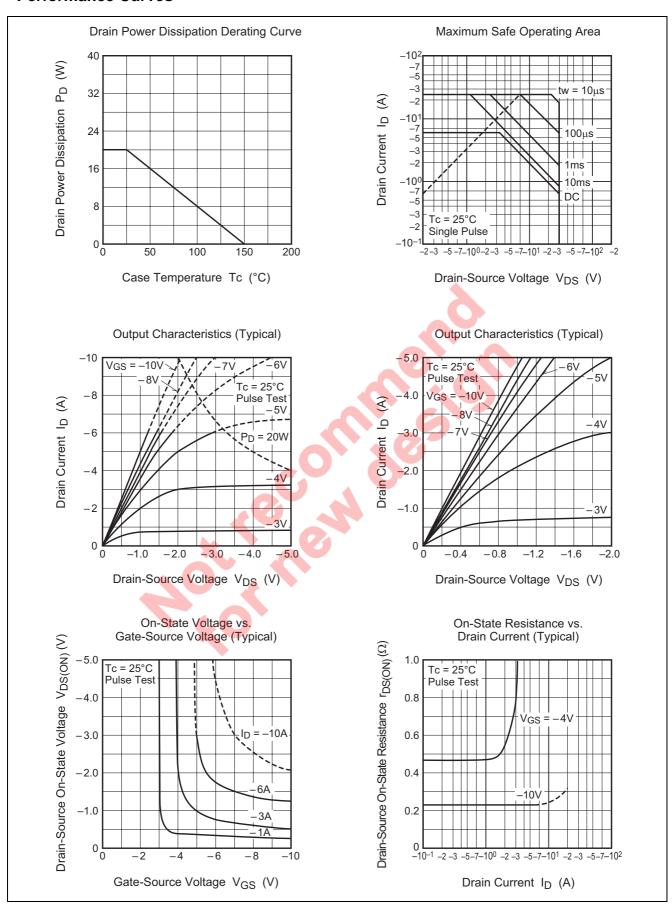
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V _{DSS}	-30	V	V _{GS} = 0 V
Gate-source voltage	V _{GSS}	±20	V	V _{DS} = 0 V
Drain current	I _D -6		А	
Drain current (Pulsed)	I _{DM}	-24	А	
Avalanche current (Pulsed)	I _{DA}	-6	А	L = 30 μH
Source current	Is	-6	А	
Source current (Pulsed)	I _{SM}	-24	А	
Maximum power dissipation	P _D	20	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

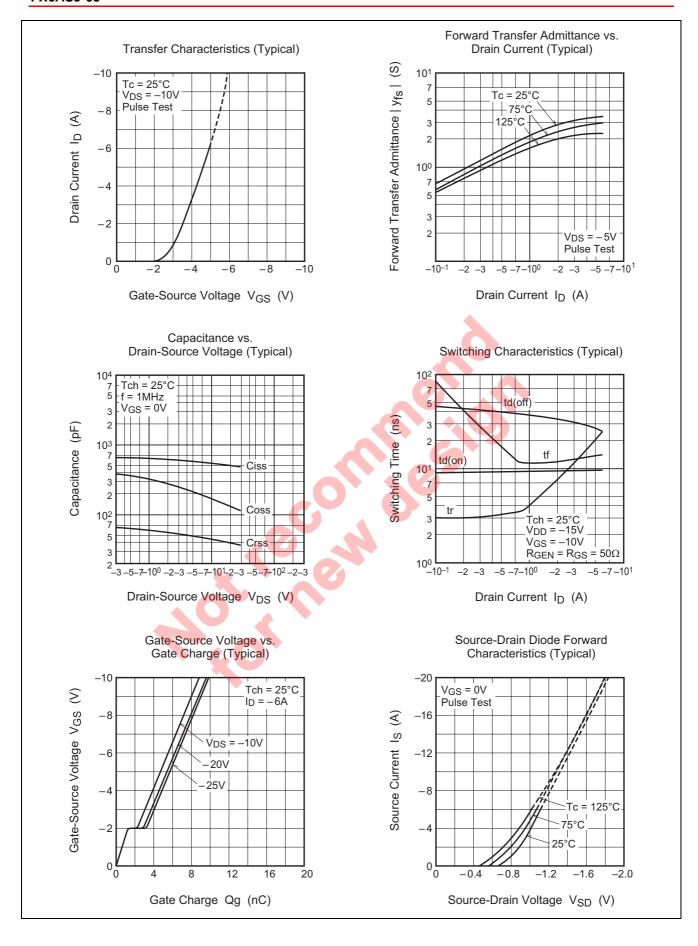
Electrical Characteristics

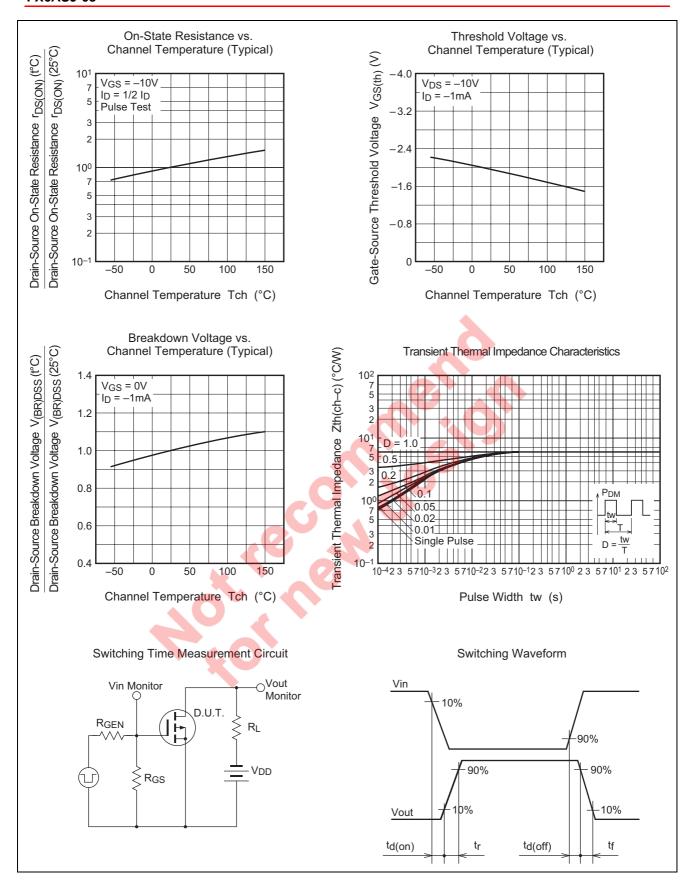
 $(Tch = 25^{\circ}C)$

Drain-source breakdown voltage Gate-source leakage current	V _{(BR)DSS}					
Gate-source leakage current	(511)500	-30	_	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$
	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I _{DSS}	_	_	-0.1	mA	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	V _{GS(th)}	-1.3	-1.8	-2.3	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	0.23	0.29	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	0.46	0.62	Ω	$I_D = -1 A$, $V_{GS} = -4 V$
Drain-source on-state voltage	V _{DS(ON)}	_	- 0.69	- 0.87	V	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y _{fs}	_	2.6	_	S	$I_D = -3 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss	_	550	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	165	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	45	_	pF	
Turn-on delay time	t _{d(on)}	_	9	_	ns	$V_{DD} = -15 \text{ V}, I_D = -3 \text{ A},$
Rise time	t _r	_	14	_	ns	$V_{GS} = -10 \text{ V},$
Turn-off delay time	t _{d(off)}	_	32	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t _f	_	14	_ (ns	
Source-drain voltage	V _{SD}	_	-1.0	-1.5	V	$I_S = -3 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	Rth(ch-c)	_	_	6.25	°C/W	Channel to case
Reverse recovery time	t _{rr}	_	40	VA	ns	$I_S = -3 \text{ A}, \text{ dis/dt} = 50 \text{ A/}\mu\text{s}$
Not lecondesion						

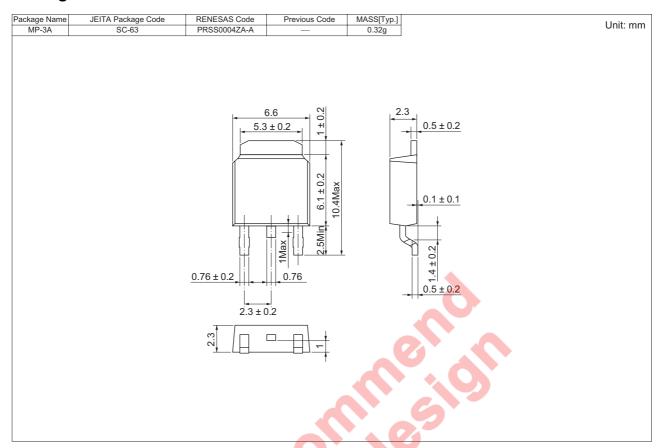
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX6ASJ-03-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX6ASJ-03

Note: Please confirm the specification about the shipping in detail.

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